

IN THE SPECIFICATION

Please replace the paragraph beginning on page 7, line 1, with the following rewritten paragraph:

A plurality of magnetic memory cells, such as the magnetic memory cells 110 of FIG. 1, are disposed in intersections between the digit lines 230 and the bit lines 240. The magnetic memory cells respectively include a rectangular free magnetic layer 140. A major axis of the rectangular free magnetic layer 140 is substantially parallel to the row direction, and a minor axis of the rectangular free magnetic layer 140 is substantially parallel to the column direction. The magnetization directions of the magnetic memory cells are shown as arrows 250 in FIG. 5.